

Features

- Uses ssc advanced PerfectMOS4 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Excellent Low Ciss
- Qualified according to JEDEC criteria

Beneficts

- High robustness and reliability
- Increases maximum current capability
- Low power loss, high power density
- Easy paralleling



100% DVDS Tested
100% Avalanche Tested

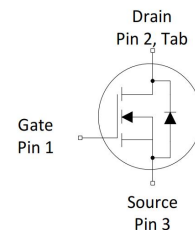
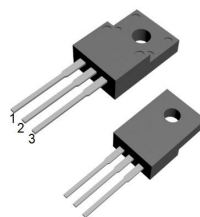
Applications

- Synchronous Rectification for AC/DC Quick Charger
- Battery management
- UPS (Uninterruptible Power Supplies)

Product Summary

V_{DS}	150V
$R_{DS(on)}@10V$ typ	5.4mΩ
I_D	106A

TO-220MF-3L



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
SW065N15MFS	SW065N15MFS	TO-220MF-3L	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	150	V
Continuous drain current	I_D	106	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		160	
$T_C = 25^\circ\text{C}$ (Package limit)		67	
$T_C = 100^\circ\text{C}$ (Silicon limit)		13	
$T_a = 25^\circ\text{C}$			
Pulsed drain current ($T_C = 25^\circ\text{C}$, $t_p = 100\mu\text{s}$)	$I_{D \text{ pulse}}$	422	A
Avalanche energy, single pulse ($L=0.5\text{mH}$, $V_{ds}=50\text{V}$)	E_{AS}	352	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation	P_{tot}	125	W
$T_C = 25^\circ\text{C}$		1.9	
$T_a = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	0.68	1.00	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	RthJA	-	-	66	°C/W	-

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	150	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	2.0	-	4.0	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	0.02	1	μA	V _{DS} =60V, V _{GS} =0V T _j =25°C T _j =150°C
Gate-source leakage current	I _{GSS}	-	±10	±100	nA	V _{GS} =±20V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	5.4	6.5	mΩ	V _{GS} =10V, I _D =20A
Transconductance	g _{fs}	-	65	-	S	V _{DS} =5V, I _D =20A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	5587	-	pF	V _{GS} =0V, V _{DS} =75V, f=1MHz
Output Capacitance	C _{oss}	-	642	-		
Reverse Transfer Capacitance	C _{rss}	-	23	-		
Gate Total Charge	Q _G	-	90	-	nC	V _{DS} =75V, I _D =100A , V _{GS} =10V
Gate-Source charge	Q _{gs}	-	35	-		
Gate-Drain charge	Q _{gd}	-	18	-		
Turn-on delay time	t _{d(on)}	-	27	-	ns	V _{GS} =10V, V _{DD} =75V, R _{G_ext} =2.2Ω, I _D =50A
Rise time	t _r	-	3	-		
Turn-off delay time	t _{d(off)}	-	58	-		
Fall time	t _f	-	5.4	-		
Gate resistance	R _G	-	1	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.8	1.2	V	$V_{GS}=0V, I_{SD}=20A$
Body Diode Continuous Forward Current	I_S	-	-	106	A	$TC = 25^{\circ}C$
Body Diode Pulsed Current	I_S pulse	-	-	422	A	$TC = 25^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	129	-	ns	$I_F=1A, dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	487	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

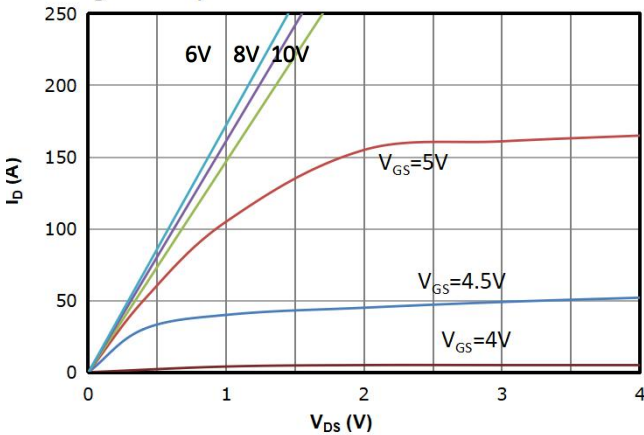


Fig 2: Transfer Characteristics

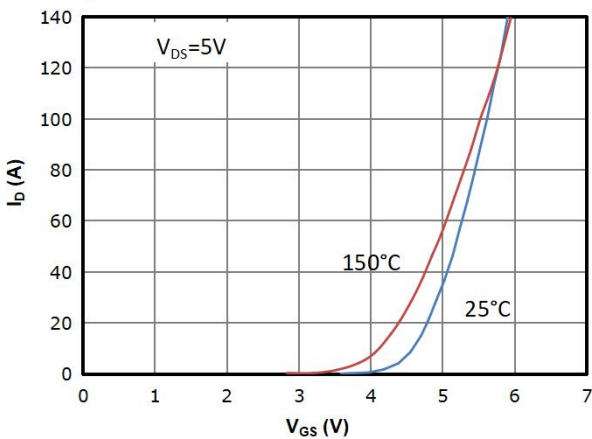


Fig 3: Rds(on) vs Drain Current and Gate Voltage

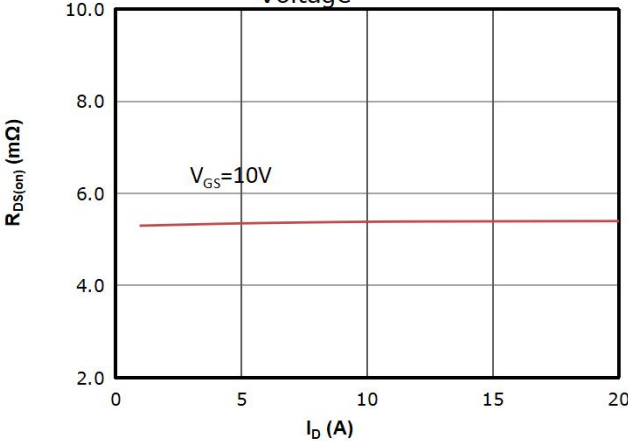


Fig 4: Rds(on) vs Gate Voltage

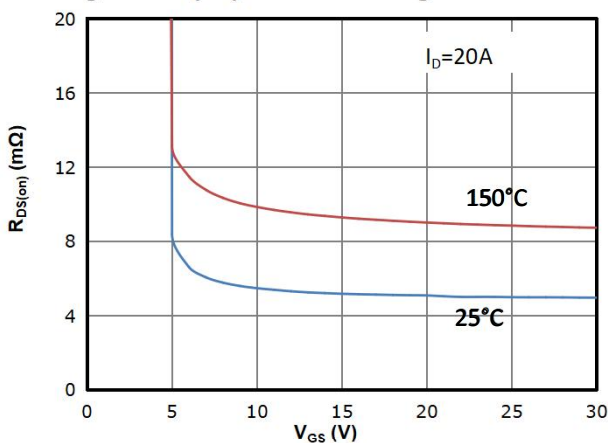


Fig 5: Rds(on) vs. Temperature

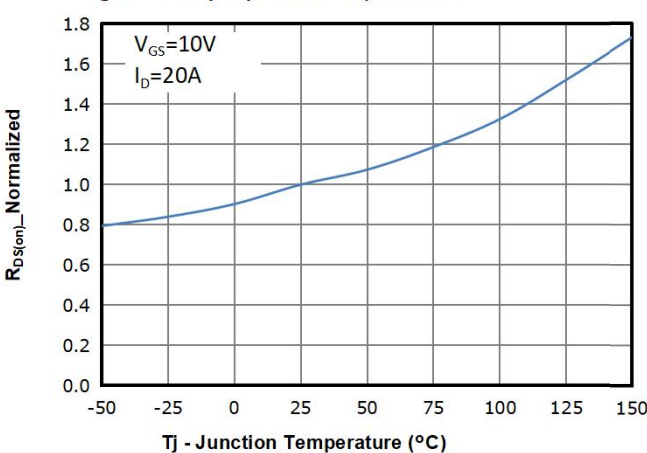


Fig 6: Vgs(th) vs. Temperature

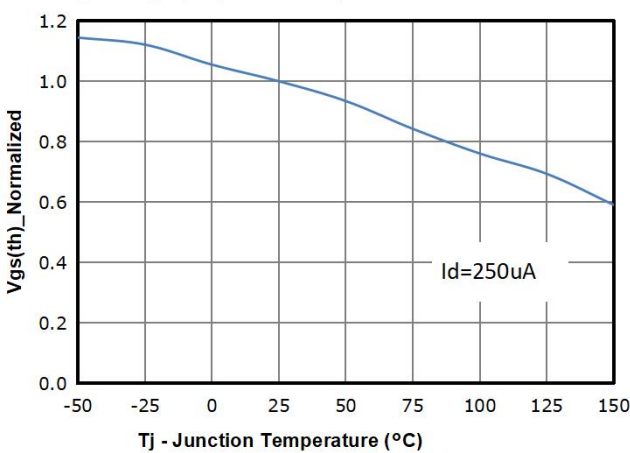


Fig 7: BVdss vs. Temperature

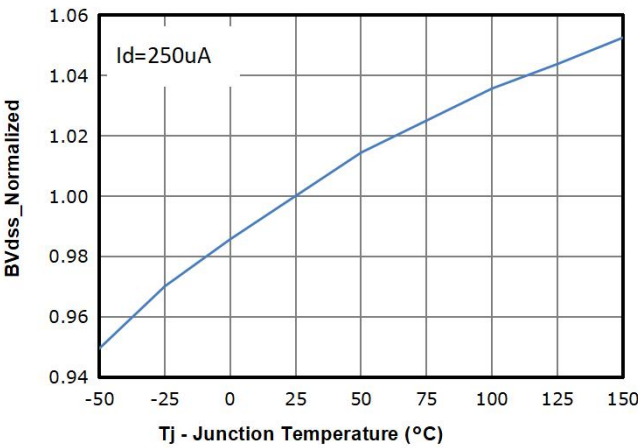


Fig 8: Capacitance Characteristics

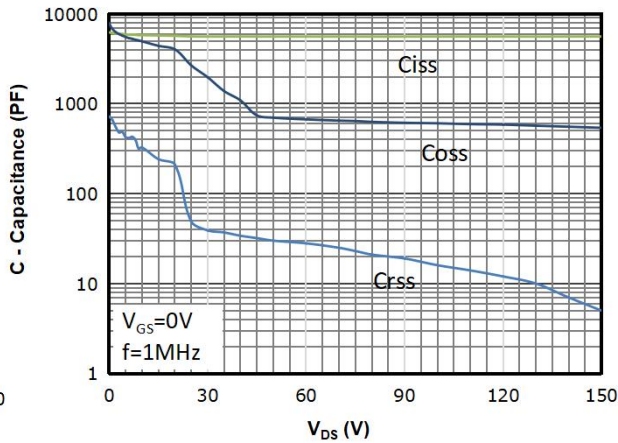


Fig 9: Gate Charge Characteristics

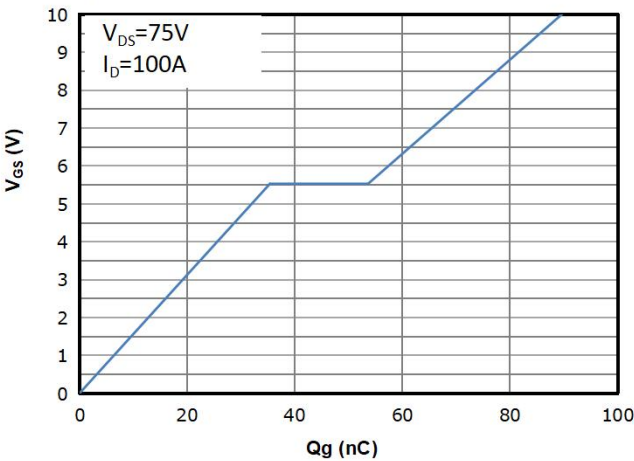


Fig 10: Body-diode Forward Characteristics

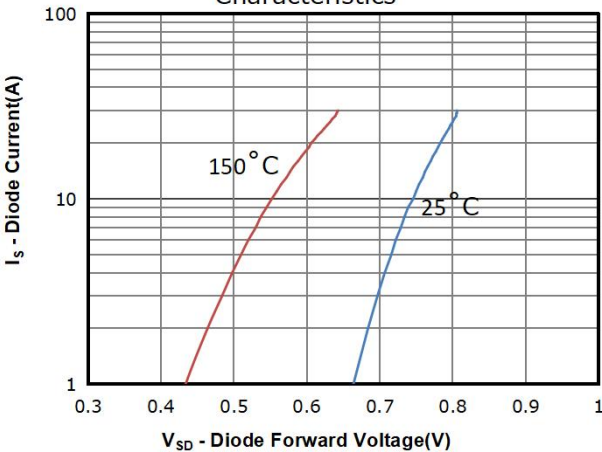


Fig 11: Power Dissipation

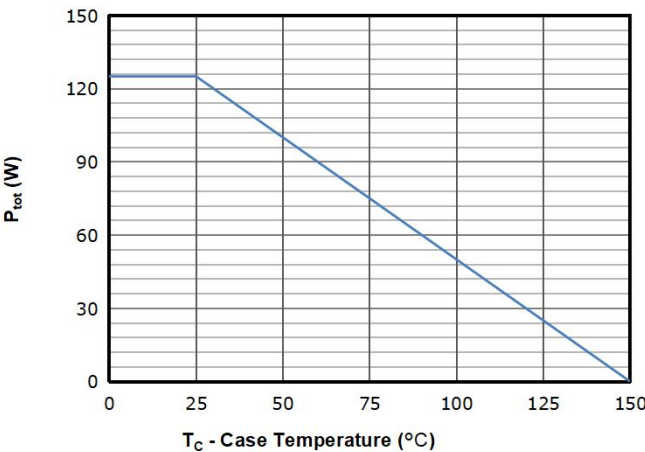


Fig 12: Drain Current Derating

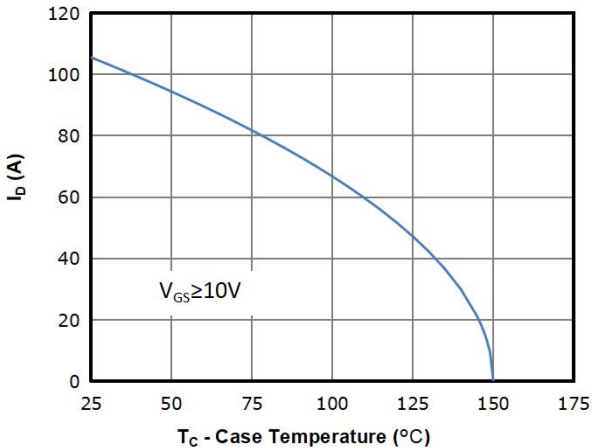


Fig 13: Safe Operating Area

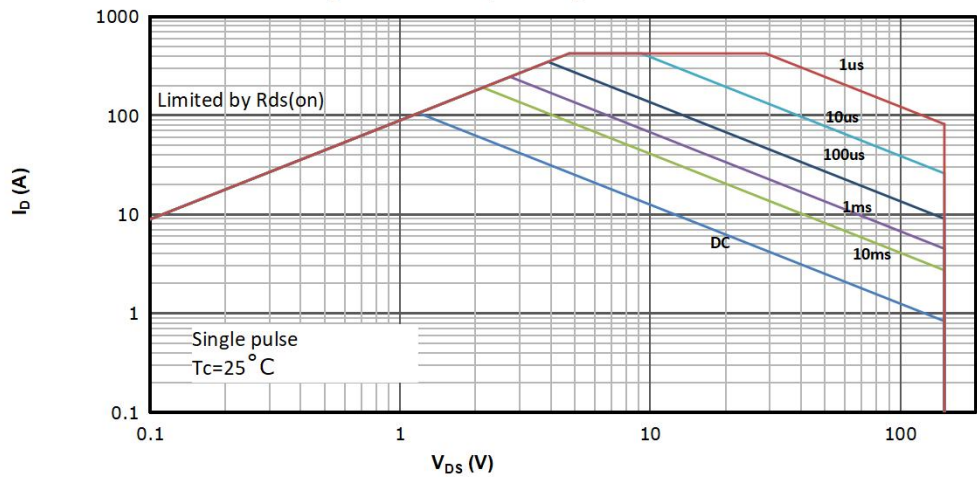
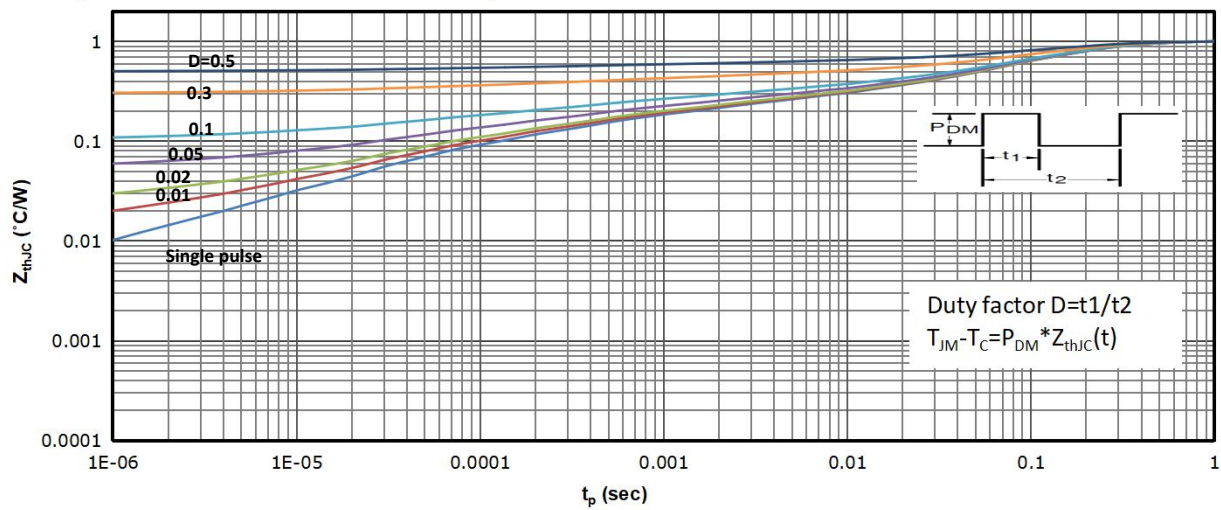
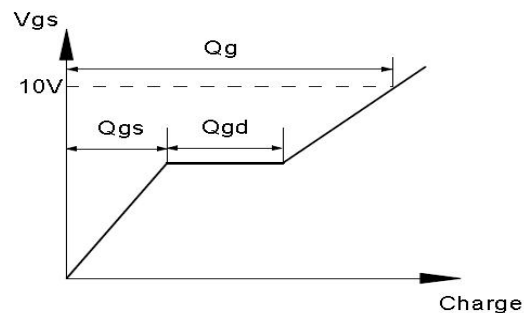
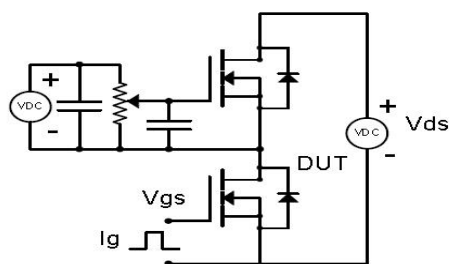


Fig 14: Max. Transient Thermal Impedance

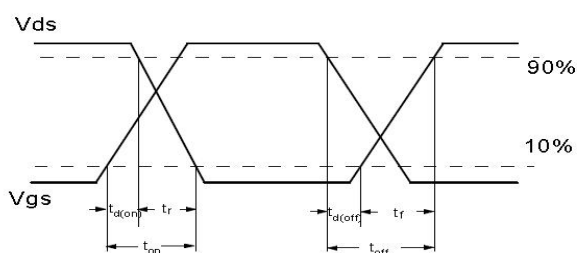
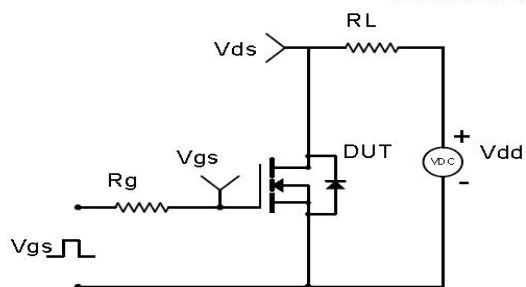


Test Circuit & Waveform

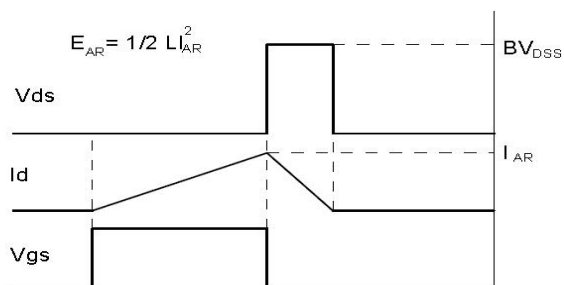
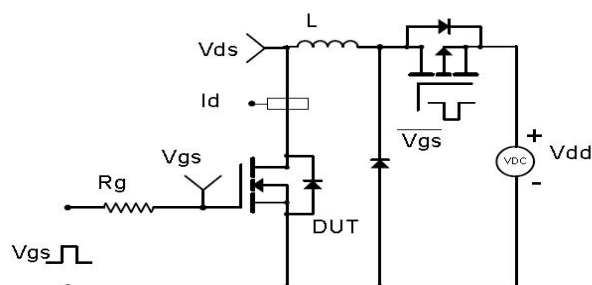
Gate Charge Test Circuit & Waveform



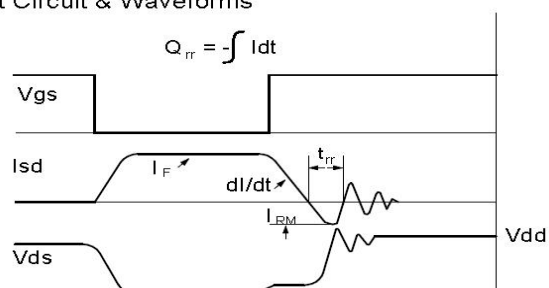
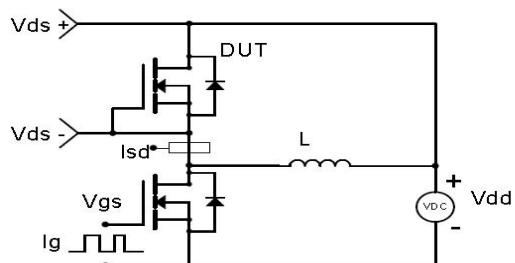
Resistive Switching Test Circuit & Waveforms



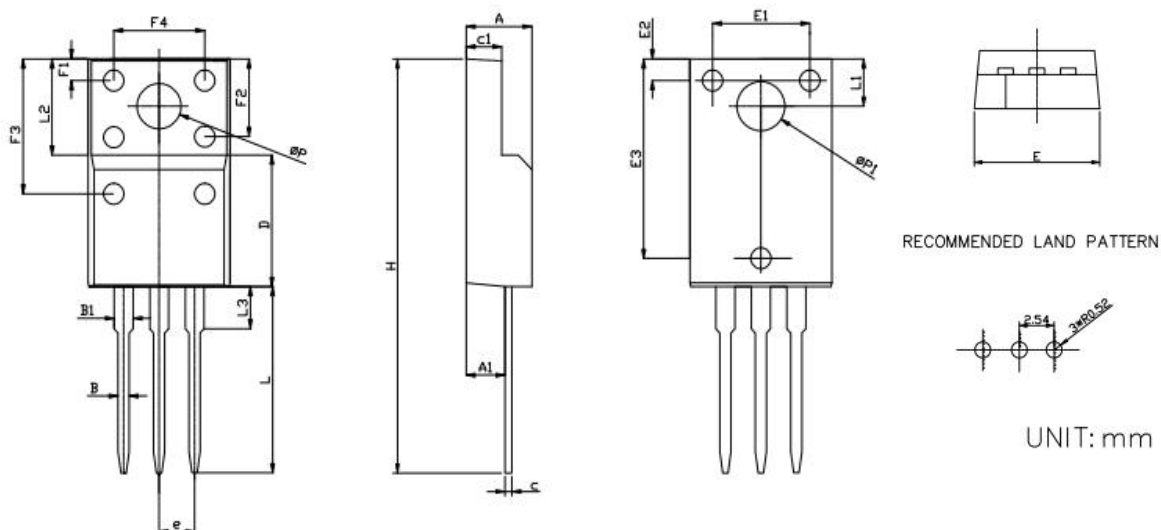
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO 220MF 3L



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.50	4.90	0.177	0.193
A1	2.63	2.89	0.104	0.114
B	0.75	0.90	0.030	0.035
B1	1.15	1.55	0.045	0.061
C	0.40	0.60	0.016	0.024
C1	2.34	2.74	0.092	0.108
D	8.87	9.47	0.349	0.373
e	2.54		0.100	
E	9.86	10.46	0.388	0.412
E1	6.86	7.06	0.270	0.278
E2	1.40	1.60	0.055	
E3	13.80	14.00	0.543	0.551
F1	1.40	1.60	0.055	
F2	5.15	5.65	0.203	0.222
F3	9.10	9.70	0.358	0.382
F4	6.70	7.30	0.264	0.287
H	28.50	29.50	1.122	1.161
L	12.58	13.38	0.495	0.527
L1	3.15	3.45	0.124	0.136
L2	6.70		0.264	
L3	2.63	3.23	0.104	0.127
φP	2.90	3.48	0.114	0.137
φP1	3.15	3.75	0.124	0.148

Revision History

Revision	Date	Major changes
1.0	2022-3-19	Release of Formal Version.
1.1	2022-12-12	change Capacitance/Gate Charge test condition and Spec

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

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